

**AMENDMENT TO THE CLAIMS**

Please amend the claims without prejudice, without admission, without surrender of subject matter, and without any intention of creating any estoppel as to equivalents, as follows.

**In the Claims:**

1. (Currently amended) A dielectric particle aggregate made of dielectric particles of BaO-TiO<sub>2</sub>-Nd<sub>2</sub>O<sub>3</sub> type dielectric or SrTiO<sub>3</sub> type dielectric, wherein each of the particles contain ZnTiO<sub>3</sub> and/or Zn<sub>2</sub>TiO<sub>4</sub> in the surface layer thereof.

Claims 2-3 (Canceled)

4. (Previously presented) The dielectric particle aggregate as claimed in claim 1, wherein the BaO-TiO<sub>2</sub>-Nd<sub>2</sub>O<sub>3</sub> type dielectric contains as principal ingredients BaO by 10 to 16 mol%, TiO<sub>2</sub> by 67 to 72 mol% and Nd<sub>2</sub>O<sub>3</sub> by 16 to 18 mol% and as auxiliary ingredients Bi<sub>2</sub>O<sub>3</sub> by 7 to 10 parts by weight and Al<sub>2</sub>O<sub>3</sub> by 0.3 to 1.0 parts by weight relative to 100 parts by weight of the principal ingredients.

5. (Previously presented) The dielectric particle aggregate as claimed in claim 1, wherein the surface layer has a thickness not greater than 50 nm.

6. (Previously presented) The dielectric particle aggregate as claimed in claim 1, wherein the dielectric particle aggregate has an average particle size of 0.4 μm to 3.0 μm.

7. (Previously presented) A method of manufacturing a dielectric particle aggregate as claimed in claim 1, comprising the steps of mixing ZnO with an aggregate of particles of a dielectric base material containing Ti and subjecting the resultant mixture to a calcining process.

8. (Original) The method of manufacturing dielectric particle aggregate as claimed in claim 7, wherein 0.5 to 10 parts by weight of ZnO is mixed with 100 parts by weight of the aggregate of particles of dielectric base material.

9. (Previously presented) The method of manufacturing dielectric particle aggregate as claimed in claim 7, wherein the calcining process is conducted in an oxygen-containing atmosphere.

10. (Previously presented) The method of manufacturing dielectric particle aggregate as claimed in claim 7, wherein the temperature of the-TiO process is 900 to 1,200°C.

11. (Previously Presented) A low temperature sinterable dielectric ceramic composition containing the dielectric particle aggregate as claimed in claim 1 by 100 parts by weight and a glass component by 2.5 to 20 parts by weight.

12. (Original) The low temperature sinterable dielectric ceramic composition as claimed in claim 11, wherein the glass component contains ZnO by 45 to 70 wt%, B<sub>2</sub>O<sub>3</sub> by 5 to 13 wt%, SiO<sub>2</sub> by 7 to 40 wt% and Al<sub>2</sub>O<sub>3</sub> by 8 to 20 wt%.

13. (Withdrawn) A low-temperature-sintered dielectric ceramic containing 100 parts by weight of dielectric particles constituting the dielectric particle aggregate as claimed in claim 1 and 2.5 to 20 parts by weight of glass component.

14. (Withdrawn) The low-temperature-sintered dielectric ceramic as claimed in claim 13, wherein the glass component contains ZnO by 45 to 70 wt%, B<sub>2</sub>O<sub>3</sub> by 5 to 13 wt%, SiO<sub>2</sub> by 7 to 40 wt% and Al<sub>2</sub>O<sub>3</sub> by 8 to 20 wt%.

15. (Withdrawn) A method of manufacturing a low-temperature-sintered dielectric ceramic comprising the step of sintering the low temperature sinterable dielectric ceramic composition as claimed in claim 11 at 880 to 1,000°C.

16. (Withdrawn) The method of manufacturing low-temperature-sintered dielectric ceramic as claimed in claim 15, wherein the glass component contains ZnO by 45 to 70 wt%, B<sub>2</sub>O<sub>3</sub> by 5 to 13 wt%, SiO<sub>2</sub> by 7 to 40 wt% and Al<sub>2</sub>O<sub>3</sub> by 8 to 20 wt%.

17. (Withdrawn) The method of manufacturing low-temperature-sintered dielectric ceramic as claimed in claim 15, wherein the sintering step is conducted on a laminate having a layer containing the low temperature sinterable dielectric ceramic composition and a layer containing metal to thereby obtain an electronic part having a laminated structure where the metal layer functions as an internal conductor.

18. (Withdrawn) The method of manufacturing low-temperature-sintered dielectric ceramic as claimed in claim 17, wherein the metal layer is made of Ag, Cu or an alloy containing at least either of them.

19. (New) The dielectric particle aggregate as claimed in claim 1, wherein  $\text{ZnTiO}_3$  and/or  $\text{Zn}_2\text{TiO}_4$  is contained only in the surface layer of the particles.

20. (New) The dielectric particle aggregate as claimed in claim 5, wherein the surface layer has a thickness not less than 10 nm.

21. (New) The method of manufacturing low-temperature-sintered dielectric ceramic as claimed in claim 7, wherein the particles of dielectric base material practically do not contain Zn.

22. (New) The method of manufacturing low-temperature-sintered dielectric ceramic as claimed in claim 7, wherein  $\text{ZnTiO}_3$  and/or  $\text{Zn}_2\text{TiO}_4$  is formed on the surface of the particles of dielectric base material in the calcining process.